PROCESS CPD109R

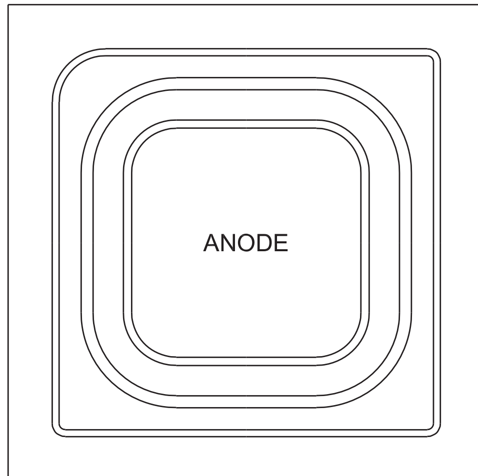
Schottky Diode

Low V_F Schottky Diode Chip

PROCESS DETAILS

Die Size	8.3 x 8.3 MILS
Die Thickness	3.9 MILS
Anode Bonding Pad Area	5.4 x 5.4 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



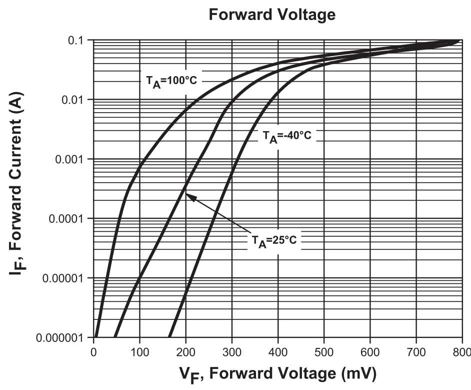
GROSS DIE PER 5 INCH WAFER
251,364

PRINCIPAL DEVICE TYPE
CFSH01-30L

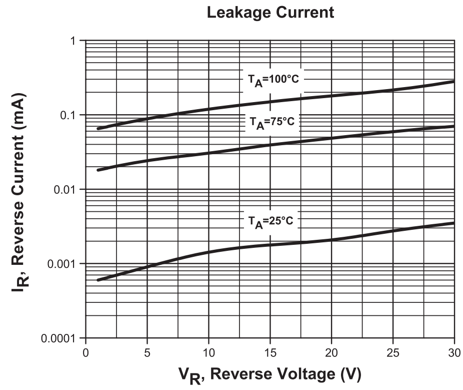
PROCESS CPD109R

Typical Electrical Characteristics

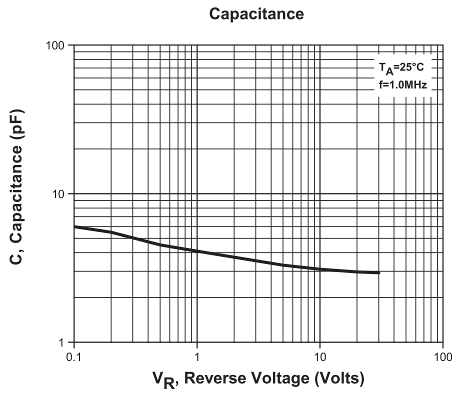
Forward Voltage



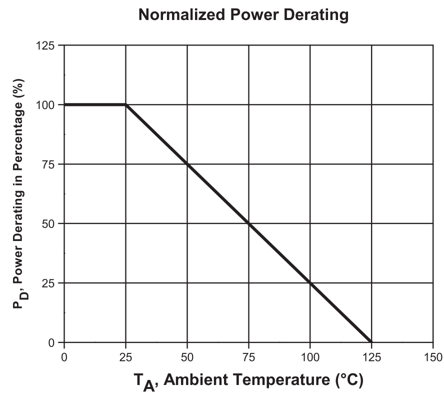
Leakage Current



Capacitance



Normalized Power Derating



R0 (13-April 2011)